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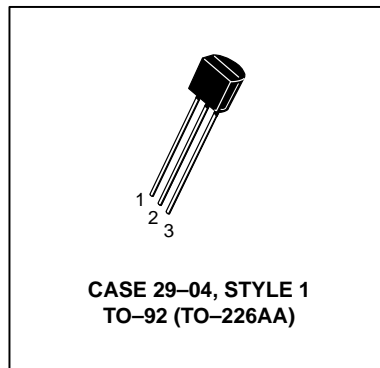
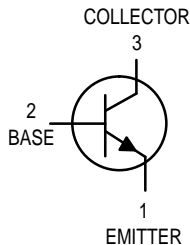
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General Purpose Transistors

NPN Silicon

2N4123
2N4124



MAXIMUM RATINGS

Rating	Symbol	2N4123	2N4124	Unit
Collector–Emitter Voltage	V_{CEO}	30	25	Vdc
Collector–Base Voltage	V_{CBO}	40	30	Vdc
Emitter–Base Voltage	V_{EBO}	5.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0 \text{ mAdc}, I_E = 0$)	$V_{(BR)CEO}$	30 25	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	40 30	— —	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ ($I_C = 2.0 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	50	150	—
	2N4123	120	360	
	2N4124			
($I_C = 50 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		25	—	
	2N4123	60	—	
	2N4124			
Collector–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{CE(sat)}$	—	0.3	Vdc
Base–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 50 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$)	$V_{BE(sat)}$	—	0.95	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	250	—	MHz
	2N4123	300	—	
	2N4124			
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	—	8.0	pF
Collector–Base Capacitance ($I_E = 0$, $V_{CB} = 5.0 \text{ V}$, $f = 1.0 \text{ MHz}$)	C_{cb}	—	4.0	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mAdc}$, $V_{CE} = 10 \text{ Vdc}$, $R_S = 10 \text{ k ohm}$, $f = 1.0 \text{ kHz}$)	h_{fe}	50	200	—
	2N4123	120	480	
	2N4124			
Current Gain — High Frequency ($I_C = 10 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	$ h_{fe} $	2.5	—	—
	2N4123	3.0	—	
	2N4124			
($I_C = 2.0 \text{ mAdc}$, $V_{CE} = 10 \text{ V}$, $f = 1.0 \text{ kHz}$)		50	200	
($I_C = 2.0 \text{ mAdc}$, $V_{CE} = 10 \text{ V}$, $f = 1.0 \text{ kHz}$)		120	480	
	2N4123			
	2N4124			
Noise Figure ($I_C = 100 \mu\text{Adc}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 1.0 \text{ k ohm}$, $f = 1.0 \text{ kHz}$)	NF	—	6.0	dB
	2N4123	—	5.0	
	2N4124			

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0%.

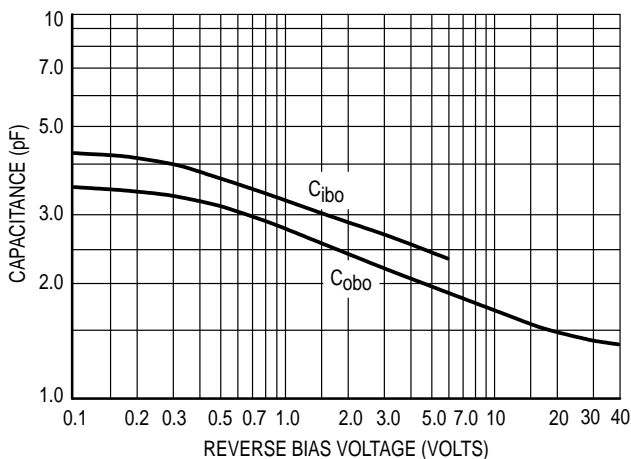


Figure 1. Capacitance

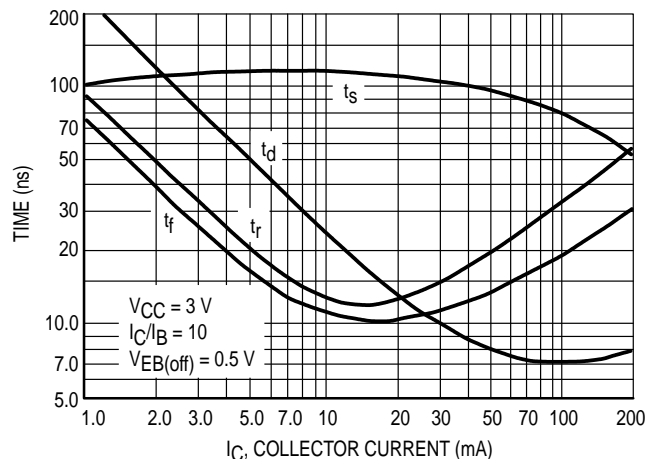


Figure 2. Switching Times

AUDIO SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

($V_{CE} = 5 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

Bandwidth = 1.0 Hz

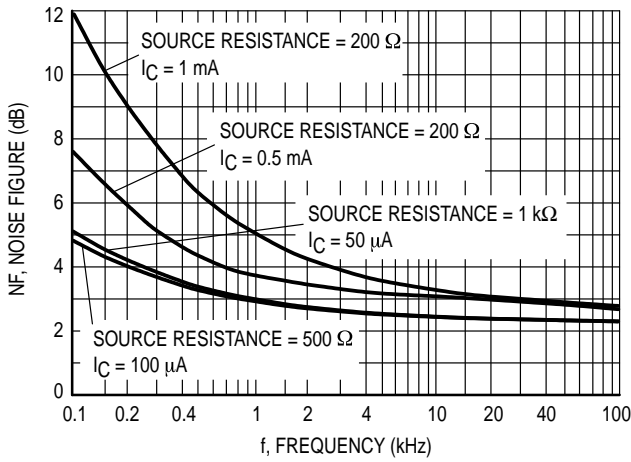


Figure 3. Frequency Variations

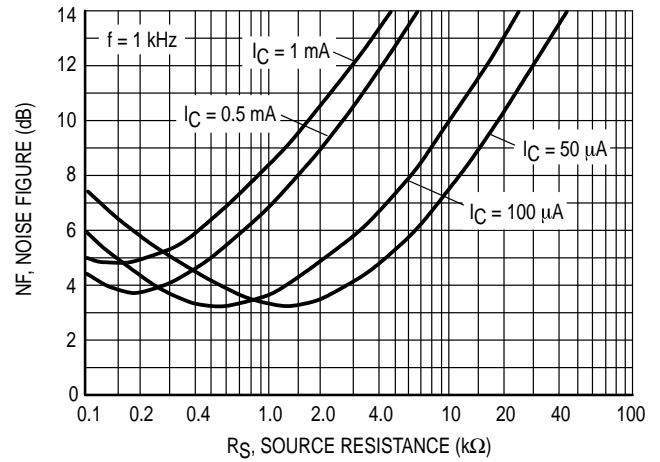


Figure 4. Source Resistance

h PARAMETERS

($V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

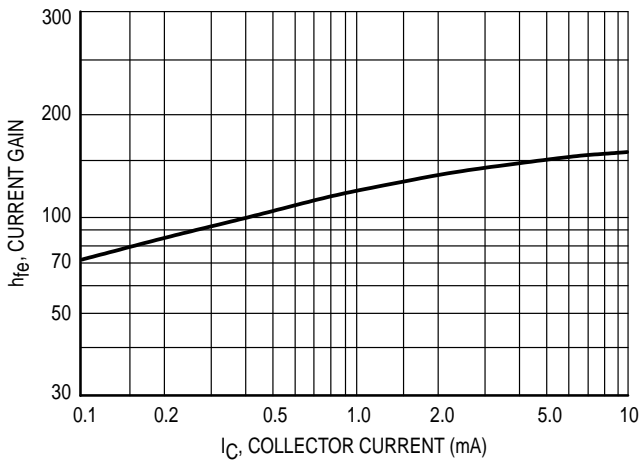


Figure 5. Current Gain

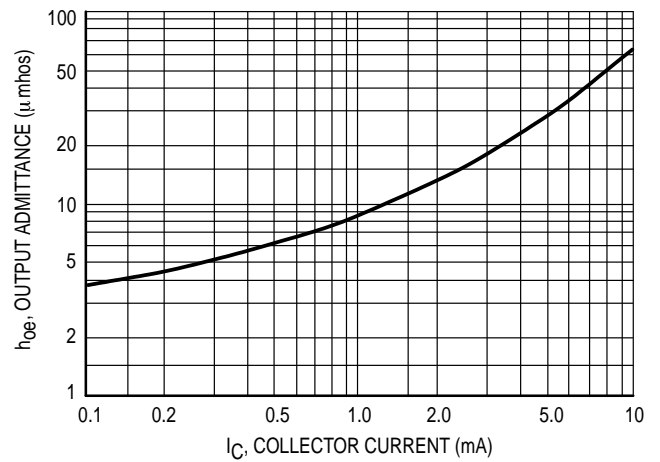


Figure 6. Output Admittance

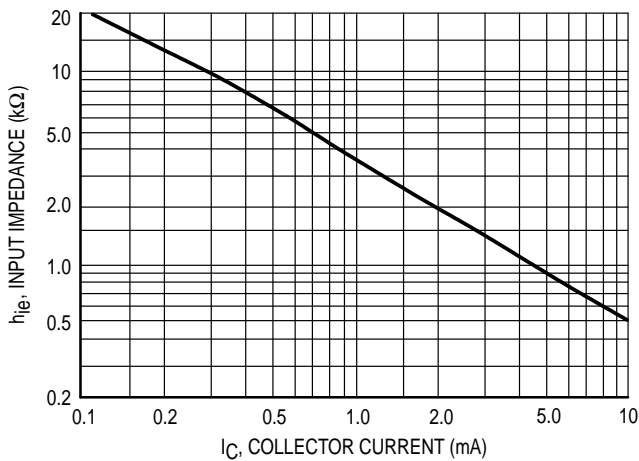


Figure 7. Input Impedance

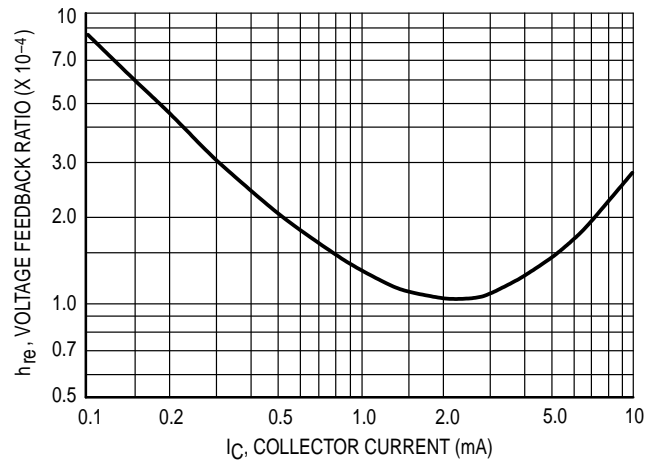


Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

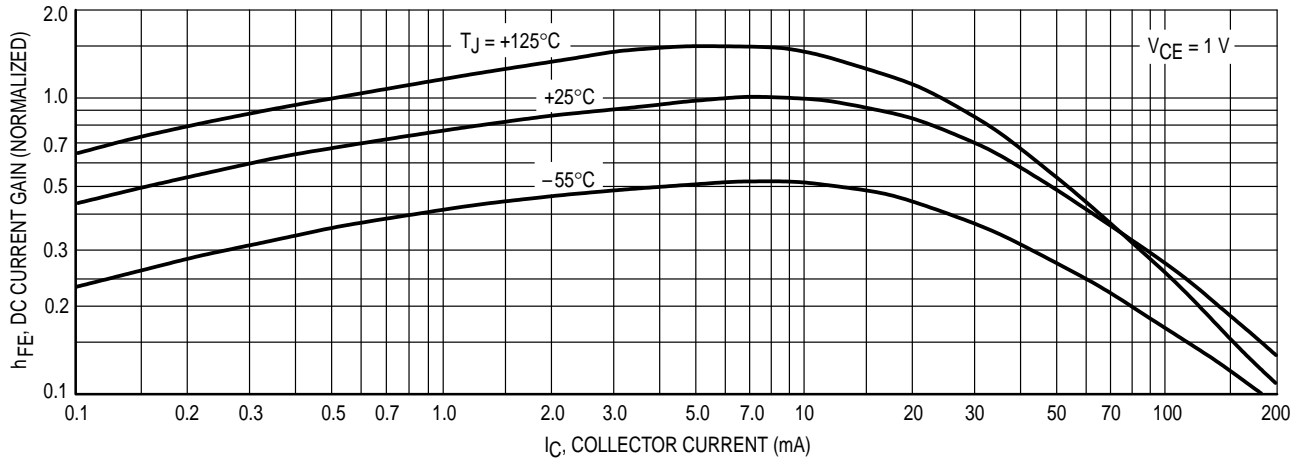


Figure 9. DC Current Gain

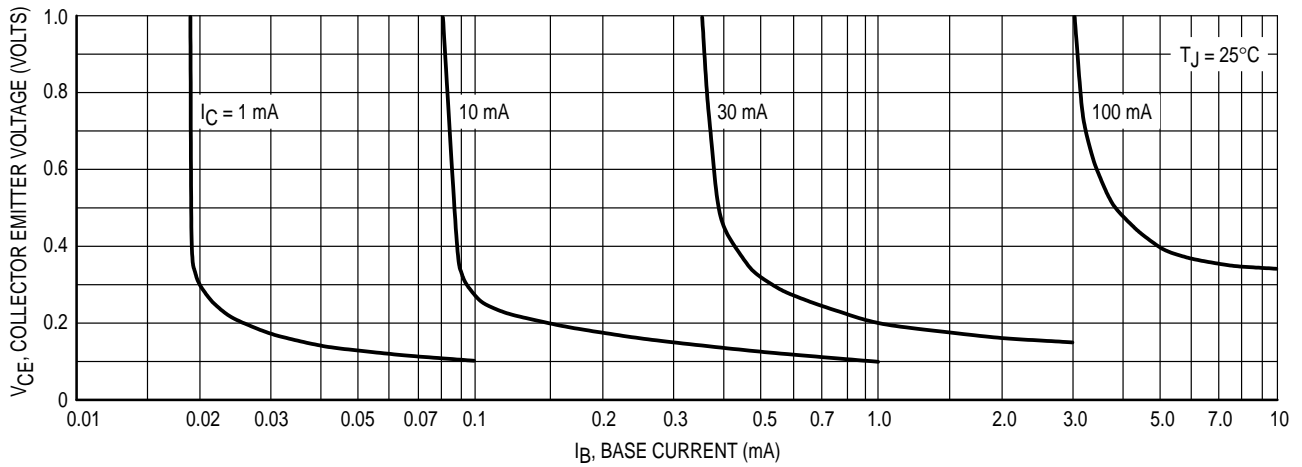


Figure 10. Collector Saturation Region

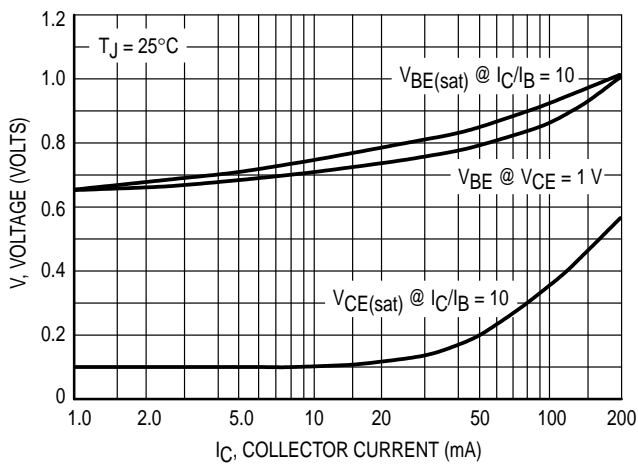


Figure 11. "On" Voltages

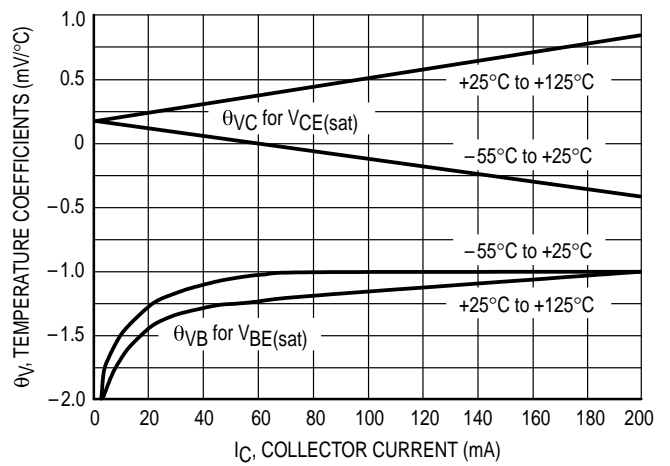
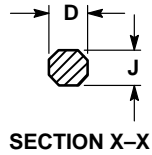
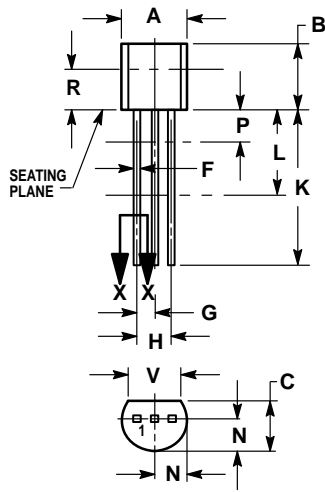


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS



**CASE 029-04
(TO-226AA)
ISSUE AD**


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K. MINIMUM LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

STYLE 1:

- PIN 1. EMITTER
2. BASE
3. COLLECTOR

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